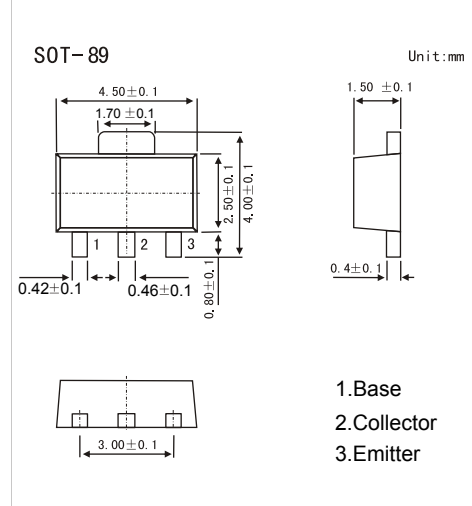


PNP Transistors

2SB1132

■ Features

- Low $V_{CE(sat)}$
- Compliments to 2SD1664



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-32	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current (DC)	I_c	-1	A
Single pulse, $P_w=100\text{ms}$		-2	A
Collector Power Dissipation	P_C *	0.5	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$

* When mounted on a 40x40x0.7mm ceramic board.

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

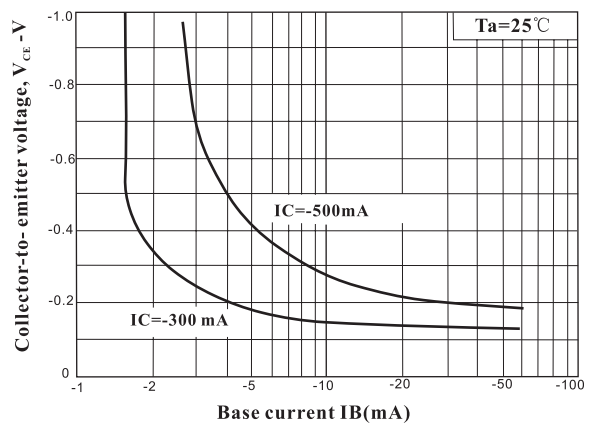
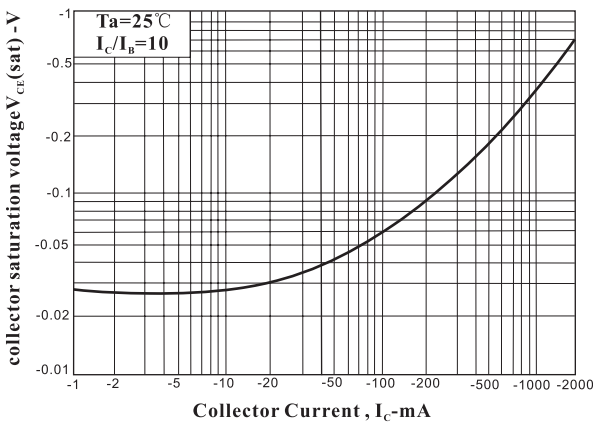
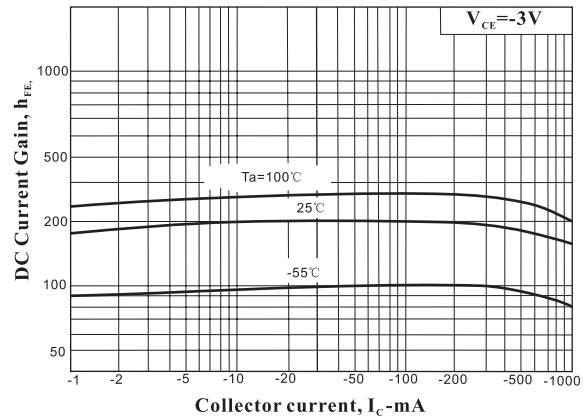
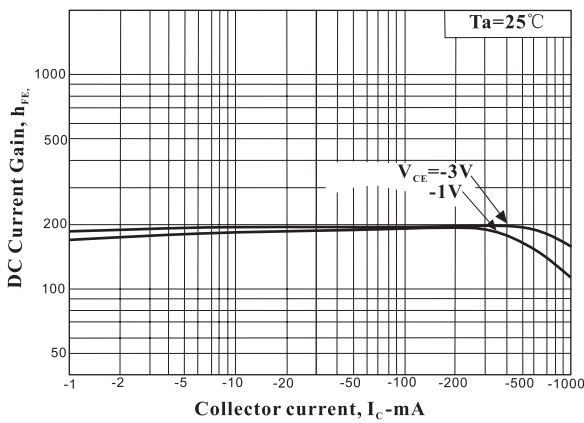
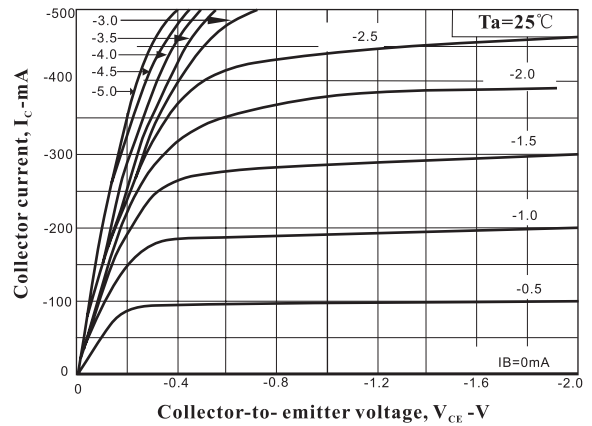
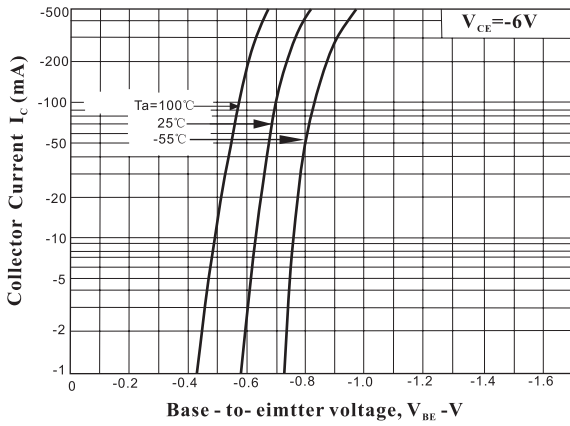
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_c = -50\mu\text{A}, I_E = 0$	-40			V
Collector- emitter breakdown voltage	V_{CEO}	$I_c = -1\text{ mA}, I_B = 0$	-32			
Emitter - base breakdown voltage	V_{EBO}	$I_E = -50\mu\text{ A}, I_c = 0$	-5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -20\text{ V}, I_E = 0$			-0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4\text{ V}, I_c = 0$			-0.5	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = -500\text{ mA}, I_B = -50\text{mA}$		-0.2	-0.5	V
DC current gain	h_{FE}	$V_{CE} = -3\text{V}, I_c = -0.1\text{A}$	82		390	
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0\text{mA}, f = 1\text{MHz}$		20	30	μF
Transition frequency	f_T	$V_{CE} = -5\text{V}, I_E = 50\text{mA}, f = 30\text{MHz}$		150		MHz

■ h_{FE} Classification

Marking	BA*		
Rank	P	Q	R
h_{FE}	82 ~ 180	120 ~ 270	180 ~ 390

2SB1132

■ Typical Characteristics





炬芯微
XUANXINWEI

SMD Type Transistors

2SB1132

■ Typical Characteristics

